

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
21 March 2002 (21.03.2002)

PCT

(10) International Publication Number
WO 02/23592 A2

(51) International Patent Classification⁷: **H01L**

(21) International Application Number: PCT/US01/41634

(22) International Filing Date: 7 August 2001 (07.08.2001)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
09/660,725 13 September 2000 (13.09.2000) US

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(81) Designated States (*national*): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, TZ, UA, UG, UZ, VN, YU, ZA, ZW.

(84) Designated States (*regional*): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— *without international search report and to be republished upon receipt of that report*

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: **METHOD AND APPARATUS FOR REDUCING IC DIE MASS AND THICKNESS WHILE IMPROVING STRENGTH CHARACTERISTICS**

(57) Abstract: A method for decreasing the mass and increasing the strength of an IC wafer assembly involves adding a polymer coating to the frontside of the wafer assembly to protect and strengthen the assembly, and removing silicon material from the backside of the wafer assembly, reducing the overall thickness of the assembly. The removal can be by backgrinding or by many other removal techniques, and in some cases is removed to a thickness less than that of the polymer coating.

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Method and Apparatus for Reducing IC Die Mass and Thickness While Improving Strength Characteristics

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Field of the Invention

The present invention is in the field of semiconductor and printed-circuit-board (PCB) manufacturing including surface mount technologies (SMT), and
10 pertains more particularly to methods and apparatus for strengthening structures while reducing mass and thickness.

Cross-Reference to Related Documents

15

The present application is a continuation-in-part (CIP) application to
copending patent application S/N 09/625,693, entitled "Method and Apparatus for
Protecting and Strengthening Electrical Contact Interfaces", which was filed on July
26, 2000, and which is incorporated herein in its entirety by reference.

20

Background of the Invention

The field of integrated circuit interconnection and packaging is one of the most
rapidly-evolving technologies associated with semiconductor manufacturing. As
25 demand for devices that are smaller and more powerful continues to increase,
pressures are put on manufacturers to develop better and more efficient ways to
assemble and package IC products. One of the more recently developed methods for
assembling and packaging IC products is known as Ball-Grid-Array (BGA)
technology. Motorola™ inc. is one of the noted pioneers of BGA technology.
30 Currently there are many companies that license BGA technology developed by
Motorola™, and Motorola and other companies continue to develop BGA technology.

BGA technology provides several advantages over more mainstream
technologies such as Fine-Pitch-Technology (FTP), and Pin-Grid-Array (PGA). One

obvious advantage is that there are no leads that can be damaged during handling. Another obvious advantage is that the solder balls are typically self-centering on die pads. Still other advantages are smaller size, better thermal and electrical performances, better package yields, and so on.

5 In BGA technology, wafers or substrates are typically protected with a non-conductive material such as a nitride layer. The die pads are exposed through the nitride layer by means of chemical etching, or by other known methods. The protective nitride layer is intended to protect the substrates from contaminants and damage. One problem with prior-art protective coatings such as a nitride layer is that
10 it is ultra-thin and does not offer any protection to the die pads themselves nor to the connection points between solder balls in the die pads.

It has occurred in the inventor that an additional protective coating, such as a protective polymer-based coating, would offer a measure of protection not provided with prior-art coatings. For example, it is desired that in addition to protecting the
15 substrates itself, die pads and soldered connections may also benefit logically from protection. However, in order to obtain the added, protective benefits from an additional coating, a unique application process must be conceived. It is to such a process that the method and apparatus of the present invention is directed.

In the development of protective coating technology for BGA devices and
20 other contact schemes the inventors have also discovered that a similar technique also provides vastly increased lateral strength for connections made to connection pads on BGA assemblies and other sorts of devices wherein connection extensions to pads are necessary. The unique coatings also provide additional rigidity for devices, both while devices (dies) are still joined on a wafer before separation, and after the die are
25 separated. The inventors have discovered that the benefits of the strengthening are such that silicon thickness can be reduced significantly after the application of such a coating, reducing overall die thickness and also mass, as well as thermal mass.

Summary of the Invention

In a preferred embodiment of the present invention a method for decreasing the mass and increasing the strength of an IC wafer assembly is provided, comprising
5 the steps of (a) adding a polymer coating to the frontside of the wafer assembly to protect and strengthen; and (b) removing silicon material from the backside of the wafer assembly, reducing the overall thickness of the assembly.

In preferred embodiments, in step (b), the silicon material is removed by grinding. Also in preferred embodiments the polymer layer may be applied by one of
10 screening, spraying, dispense and spinning, or injection into a mold.

In some cases steps are provided for adding contact extensions to contact regions before adding the polymer coating, and planarizing the polymer coating after addition to expose the contact extensions. In some of these embodiments there is a step for adding second contact extensions from the exposed contact extensions after
15 planarizing.

In another aspect of the invention an IC die is provided, comprising contact extensions added to contact regions on a front surface at contact interfaces, a polymer layer on the front surface supporting, protecting and strengthening the extensions and contact interfaces, and a silicon portion having a thickness significantly less than
20 conventional silicon-based dies.

In some cases thickness of the silicon portion is less than the thickness of the polymer layer.

In various embodiments of the present invention taught in enabling detail below, for the first time a method is provided whereby contacts added to IC die,
25 resulting in an interface typically of dissimilar materials, may be protected and strengthened, and the overall thickness of such die may then be reduced, providing significant advantages.

Brief Description of the Drawing Figures

Fig. 1A is a perspective view of a wafer with die pads according to prior art.

Fig. 1B is an expanded and broken view of the wafer of Fig. 1A illustrating a
5 die-pad exposed through a nitride coating.

Fig. 2 is a broken view of a BGA assembly with a protective overcoat
according to an embodiment of the present invention.

Fig. 3A is a plan view of the wafer of Fig. 2 with a protective overcoat applied
as a first step according to an embodiment of the present invention.

10 Fig. 3B is a plan view of the coated wafer of Fig. 3A with coated areas
removed in areas to expose the die pads.

Fig. 3C is a plan view of the coated wafer of Figs. 3A and 3B with solder balls
in place according to a third step.

Fig. 4 is a process diagram illustrating processing steps a through e for coating
15 and creating die pad openings according to another embodiment of the present
invention.

Fig. 5A is a section view of a vacuum enhanced coating apparatus for applying
a protective overcoat to a BGA assembly according to a preferred embodiment of the
present invention.

20 Fig. 5B is a detailed view of a portion of Fig. 5A.

Fig. 6a-f illustrates a series of steps in practicing the present invention.

Fig. 7 illustrates a general case of adding contact extensions to contact pads in
an embodiment of the present invention.

Fig. 8 illustrates the practical result of backgrinding after adding a protective
25 layer.

Fig. 9 illustrates final testing of dies by probe in an embodiment of the present
invention.

Description of the Preferred Embodiments

Fig. 1A is a idealized perspective view of a coated wafer 9 with die pads 11 according to the prior art. The skilled artisan will recognize that the pads have
5 been very much exaggerated in this view to be able to provide some detail. In this example of prior art wafer 9 is coated with a thin, protective layer that is nonconductive, such as a nitride layer 13. Die pads 11 are illustrated in an array on wafer 9. Typically, die pads 11 are nitride coated along with wafer 9, which may be a rectangular substrate instead of an actual wafer. After nitride coating, die pads 11 are
10 exposed by such as an etching process.

Fig. 1B is an expanded and broken view of one pad 11 of Fig. 1A, shown in perspective, illustrating the pad exposed through the nitride layer. In this detail, a die pad 11 can be seen recessed beneath the thickness of nitride coating 13. It is noted herein, that die pad 11 is completely exposed, meaning that there is no protective layer
15 above any of the land occupied by die pad 11. When a solder ball (not shown) is placed on die pad 11, certain real estate of die pad 11 along with the soldered area between the ball and die pad 11 will be exposed, and therefore vulnerable to damage and contamination. A goal of the present invention is to provide a process that according to various embodiments, which are described in enabling detail below, may
20 be used to successfully apply a protective coating layer in addition to the standard hard protective layer such as the nitride layer described above.

Fig. 2 is a broken view of a portion of a BGA assembly 14 with a protective overcoat 17 according to an embodiment of the present invention. In this example of the present invention, BGA assembly 14 exhibits 2 die pads 11 having solder balls 15
25 adhered thereto. A protective coating 17 is, in a preferred embodiment, a polymer-based coating such as a polyamide coating. In other embodiments, other polymer-based coatings may be used such as are known in the art and available to the inventor. This example illustrates a preferred embodiment, wherein protective coating 17 coats the substrate and the normally exposed area of each die pad 11 around solder balls 15
30 and also around the perimeter of each solder ball 15.

A nitride coating 13, which is illustrated in Figs. 1A and B, is illustrated here as coating the substrate portion of assembly 14 with the coating extending up over the attached die pads. It may be assumed herein, that a portion of coating 13 has been removed by any one of several known methods in order to clear to an appropriate area
5 on the upper surfaces of each die pad 11 for placement and reflow of solder balls 15. Protective coating 17 is illustrated as *over coating* nitride layer 13 and encompassing the lower peripheral areas of solder balls 15. A height dimension D illustrates the thickness of coating 17, which may be anywhere from 1 to 3 mils thick in a preferred embodiment. Overcoat 17 functions to protect any exposed pad areas as well as a
10 portion of solder balls 15.

In practice of the present invention, the inventor has isolated three basic processes that are useful to successfully apply protective coating 17 to BGA assembly 14. Fig. 3A is a plan-broken view of wafer 14 of Fig. 2 with a protective overcoat applied as a first step according to an embodiment of the present invention. Fig. 3B is
15 a plan-broken view of coated wafer 14 of Fig. 3A undergoing a process to expose covered die pads in a second step. Fig. 3C is a plan-broken view of coated wafer 14 of Fig.'s 3A and 3C with solder balls in place according to a third step. The examples of Fig. 3A, 3B, and 3C illustrate a general 3-part process for the over coating wafer 14, removing material to expose die pads, and then screening the solder balls into
20 place for a re-flow operation.

Referring now to Fig. 3A, wafer 14 is illustrated with protective coating 17 already applied. It may be assumed herein, although not specifically illustrated, that die pads 11 of Fig. 2 and nitride coating 13 of Fig. 2 are present on wafer 14 before application of protective coating 17. Coating 17 in a first step completely covers die
25 pads 11 and nitride coating 13. Coating 17 may be a Polyamide coating or a similar polymer-based coating as described above. Coating 17 may be applied by any one of several processes, such as by vacuum deposition process, a spin-on process, or by virtue of other known methods.

Referring now to Fig. 3B, protective coating 17 is partially removed over the
30 land areas above each die pad attached to wafer 14. This process may be a laser

process, a plasma-etch process, or a chemical-etch process. In both the plasma-etch and chemical-etch processes, a mask is used to protect portions of coating 17 not covering die pads. These portions are represented herein by element number 19. Areas where material has been removed are represented herein by element number 21.

5 Once die pads are exposed, they are ready to accept solder balls.

Referring now to Fig. 3C, wafer 14 is illustrated with solder balls 15 screened in place and ready to be re-flowed onto the associated die pads. A re-flow process uses heat to effect the solder connections between balls 15 and associated die pads. The process described above with respect to Figs. 3A-3C may be used to according to
10 one embodiment, to protect any BGA assembly.

Fig. 4 is a process diagram illustrating processing steps a through e for coating and creating die pad openings according to another embodiment of the present invention. In step a, wafer 14 is coated with a photoresist coating represented herein by element number 23. As described in Fig. 3A above, it may be assumed that die
15 pads (11) and a standard nitride layer (13) are present in this step. This photoresist process may be accomplished using a standard screen-printing technique. It is noted herein that photoresist 23 is applied before applying a protective coating (17).

In step b, a masking technique is used to cover areas of photoresist that are directly over die pads (11). Through development of photoresist (23) with a
20 protective mask applied, resist islands are formed as represented by element number 25 in this step. Resist islands 25 are present areas of photoresist left directly over die pads (11) after developing.

In step c, protective coating 17 is applied at substantially the same thickness as photoresist 25. This process of coating fills in the areas in-between resist islands 25,
25 such areas representing real estate of wafer 14 not occupied by a die pad (11).

In step d, a second masking technique is used to protect the areas coated with protective coating 17 in step c. At this point in the process, resist islands 25 are chemically developed, and then etched away exposing associated die pads (11) leaving all other real estate untouched. In step e, solder balls 15 are screened in place
30 over die pads (11) as described with reference to Fig. 3C. At this point of the process,

a re-flow operation to permanently attach solder balls 15 to die pads (11) may begin. The process represented herein by Fig. 4, illustrates a process for applying protective coating 17 according to yet another embodiment of the present invention.

Fig. 5A is a section view of a vacuum-application and coating apparatus 27 for
5 applying protective overcoat 17 to a BGA assembly according to a preferred
embodiment of the present invention. Vacuum-application and coating apparatus 27,
hereinafter referred to as simply apparatus 27, is provided and adapted to enable an
automated coating process to be performed on a BGA assembly *after* re-flow.
Apparatus 27 comprises an upper plate 29, a lower plate 31, and a vacuum seal 33. In
10 a preferred embodiment both plate 29 and 31 are manufactured of stainless-steel or
other durable metals. Plates 29 and 31 may be circular, or rectangular in shape. Other
shapes may be employed as well.

In operation a BGA assembly 32, with solder balls in place, is enclosed by
plate 29 and 31 fitted together using a seal 33. It may be assumed herein that either
15 plate 29 or plate 31 has an o-ring-style groove provided on its mating surface,
generally around the perimeter, such that seal 33 may be properly retained and
facilitated. In one embodiment, both mating surfaces of plates 29 and 31 may be
grooved to facilitate seal 33. In still another embodiment, a metallic sealing apparatus
may be used instead of an o-ring.

20 Plate 29 and 31 are fitted together over seal 33 to form apparatus 27, and the
plates may be held together by any of several methods, such as by bolts or by clamp
mechanisms. A chamber formed within apparatus 27 after assembling contains at
least one BGA assembly. In one embodiment, many BGA assemblies may be
introduced into the formed chamber for processing. The height of an internal
25 processing area formed within apparatus 27 after assembly is sufficient to
accommodate the height of a BGA assembly without damaging the assembly.

Plate 29 has a compliant layer of material, illustrated herein as compliant layer
37 affixed thereto and covering the area over the ball array of an enclosed part. This
compliant layer 37 may be a rubberized material, a polymer-based material, or any
30 other suitable material having compliant characteristics. The purpose of compliant

layer 37 on plate 29 is to protect the upper portions of solder balls (15) of a BGA assembly or assemblies inserted into apparatus 27 for processing. The dimensions of the plates are such that, when the plates are closed, the compliant layer forms over the upper portion of each solder ball as may be seen in Fig. 5B.

5 Upper plate 29 has an injection port 37 provided therethrough, which opens into the vacuum chamber formed within apparatus 27. Port 37 is adapted to enable injection of an uncured protective coating material 17, in liquid form, into the vacuum chamber during processing. In one embodiment, there may be more than 1 injection port 37 provided within plate 29. Lower plate 31 has a vacuum port 35 providing
10 therethrough, which opens into the vacuum chamber formed within apparatus 27. Port 35 is adapted to connect a vacuum pumping apparatus (not shown) to enable a vacuum to be drawn within apparatus 27. In one embodiment, there may be more than one vacuum port provided within plate 31.

In practice of the present invention, at least one BGA assembly complete with
15 re-flowed solder balls is placed onto the surface of plate 31. Plate 29 is urged into to plate 31 over seal 33 and bolted or clamped together with the BGA assembly or assemblies inside. A vacuum is then drawn by virtue of port 35. The protective coating 17 is injected through port(s) 37 to the internal chamber coating the inserted BGA assembly or assemblies.

20 Fig. 5B is an expanded view of one edge of the assembly shown in Fig. 5A. In this expanded view, wafer 14 is shown with one solder ball 15. Compliant layer 37 forms over the top of solder ball 15 and protects the covered area of ball 15 from being coated with injected coating 17, in a manner that, when released, the solder balls will be exposed on the coated parts. The top surface of solder ball 15 is required to be
25 free of coating as this area is used for lead connection. However, the remaining real estate of wafer 14 and solder ball 15 is covered with protective coating 17 during this back-filling operation. after back-filling with the protective coating material in liquid form, the material is cured before the molds are opened.

It will be apparent to one with skill in the art that apparatus 27 may be
30 manufactured of a size such as to facilitate the processing of a number of BGA

assemblies simultaneously. In one embodiment apparatus 27 may process only a few assemblies, or perhaps one assembly at a time. Once processing is completed within apparatus 27, BGA assemblies are removed from apparatus 27 by unbolting or unclamping apparatus and pulling apart plates 29 and 31 revealing completed BGA assemblies. A tracking operation may be used to remove excess coating.

In yet another embodiment of the invention for a method is provided for protecting a BGA assembly in a manner that increased strength is also provided. This method is illustrated herein with the aid of Figs. 6a through 6f. Fig. 6a illustrates a wafer 41 with balls 45 placed and soldered to solder pads, with a nitride layer 43 in place, as is known in the art. Fig. 6b shows the assembly of Fig 6a with a protective layer 47 applied according to embodiments to the present invention as described above. Layer 47 may be applied by screening, spraying, dispense and spinning, by backfilling, or in any of several other ways. Preferably, layer 47 completely covers all balls in the ball grid array.

In Fig. 6c a machining operation is illustrated using a grinding or cutting wheel 49 to remove a portion of layer 47 and enough of each ball in the ball grid array that each ball is now exposed as a flat pad even with the upper machined surface of layer 47. Fig. 6d shows the assembly of Fig. 6c completely planarized.

After planarization, solder material is applied over each exposed solder ball machined surface. Fig. 6 e illustrates a solder pad 51 in place over each solder ball in the assembly. Solder islands 51 may be applied by screen printing paste, by plating, or by direct solder ball attachment. Preferably the new solder material may have a melting point equal to that of the original solder balls, or a lower melting point.

After the new solder material is applied, that material is re-flowed, such that the new ball grid array surface is created over the original. The original solder balls are now completely encapsulated in the material of layer 47, and the original wafer surface and all of the elements of that surface are very well protected. Additionally, the new array is much more robust and strong than the original, because all stress points have now been redistributed away from the wafer surface.

In the embodiments described above, ball-grid-array (BGA) applications have been emphasized and used as examples. The invention in its various aspects, however, has application far beyond BGA assemblies, and is broadly applicable to all situations wherein electrical attachment needs to be made to specific areas on any surface. Attachment by solder balls in BGA technology is described above, but attachment may also be made by other means, such as by wire bonding in many instances. The methods are not limited to wafer and die surfaces, either, and may be applied to printed circuit boards of various kinds and other electronic connection schemes as well.

10 Broadly speaking, in any case where contact areas are exposed for attaching electrical connections the present invention has application. Fig. 7 illustrates perhaps the broadest case. In Fig. 7 a surface 53 of a device 55 has one or more connector pad areas 57, to which electrical connection needs to be made. One such connector area is shown, but there may of course be many more, as in BGA technology. One however, 15 is sufficient to practice the present invention.

In this broad example, pad 57 is typically of a material that can be applied by a deposition technique, and the material that must be used for a connecting extension 59 is typically of a different material. In the case of BGA technology extension 59 is solder material. Because of this, the interface of the two materials at pad 57 is not 20 capable of sustaining significant horizontal stress, and this leads to many physical failures. In the example shown, extension 59 is made just as in the prior art, and may be a solder ball, a gold wire, or some other sort of contact extension.

In the present invention, after contact extension 59 is applied, a polymer protective and strengthening material 61 is applied, which may be done by any one of 25 several methods as have been described in the present application above. Typically material layer 61 is applied to a thickness such that extensions 59 are completely encapsulated, then a removal technique is employed to planarize surface 63, exposing extension 59 again. The result of this step is a planarized surface 63 with new contact areas 65.

In a final step a new contact extension 67 added to contact area 65, and this extension can now typically be of the same material as extension 59, such that the juncture at area 65 may be of contiguous material, making a very strong juncture, as opposed to the weak juncture at pad 57. The weak juncture at pad 57, however, is
5 now encapsulated by layer 61, and thus greatly strengthened.

In summary, by adding an extension to pads 57, even though the interface between the extension and the pad may be fairly weak, then adding a polymer layer 61, the weak juncture can be strengthened. Then new extensions can be added with an interface that is much stronger than the original, providing thereby a very much more
10 durable mechanism, while at the same time protecting the original surface and interfaces from environmental effects.

Improving Strength While Reducing Thickness and Mass

15

In another aspect of the present invention a method and apparatus is provided wherein integrated circuits may be improved in electrical characteristics and at the same time reduced in overall thickness and mass without sacrificing strength or integrity.

20

Referring now to Figs. 6a through 6f, which show the progression of steps in a preferred embodiment for adding a protective layer to a wafer having devices implemented thereon, attention is once again drawn to the fact of adding a polymer layer to an IC wafer after extending contact regions away from the top surface of the wafer. As was previously described, the polymer layer, having been applied in a
25 preferred embodiment to a thickness greater than the height of the contact extensions, as shown in Fig. 6b, may be planarized in any of a number of ways, such as by machining, exposing a portion of each of the contact extensions, to which electrical contact may subsequently be made. The general process of planarizing by machining is illustrated in Fig. 6c, and a planarized wafer in section is shown in Fig. 6d.

As was described above, the materials at the surface of a wafer, to which a contact extension may be joined, are typically different than the materials that are desirable for making such an extension, such as solder balls for example, in the processes classed as ball-grid array (BGA) processes. The natural result is that the integrity of the original interface between a contact pad and the extension material is relatively low. That is, there is typically little lateral or vertical strength in such joints, and the resulting system is subject to deterioration and damage from many different causes and directions. For example, rough handling, vibration, and the like.

It was described above in preferred embodiments how the polymer layer, encapsulating the original interface of a contact extension, such as a solder ball, to a contact region on a die on a wafer, stabilizes and increases the strength of the original joint, as well as providing environmental protection for the circuitry in dies on a wafer. After planarizing a new contact extension can be made, typically using the same material as the first extension, providing a very strong and sure joint, because, for one reason, the joint can be contiguous. That is, in joining solder to solder, for example, there will be no dissimilar-material interface, but a continuous solder joint.

In a new aspect of the invention it is recognized that the polymer layer provides even more strengthening than was previously described. The polymer may be of a material having considerable strength when cured, and thus stiffens the wafer substantially. It is well known that silicon as used in wafers for IC manufacture is a brittle and vulnerable material. Not so the polymers that may be used for adding a protective layer in embodiments of the present invention.

The result of adding a polymer coating is that a wafer or die with the added coating is significantly stronger and more resilient than the substantially silicon-alone original structure. As a result one may backgrind such wafers to reduce the overall thickness of the die without sacrificing strength and endurance of the structure. Reducing the relative thickness of the silicon portion of the resulting overall structure by such backgrinding also has a beneficial effect of improving the electrical characteristics of the integrated circuits, because silicon is a poor conductor. The reduced thickness also provides a structure with significantly reduced thermal mass.

Figs. 8a through 8c illustrate the steps and practical result of backgrinding after adding a polymer layer. Fig. 8a shows a section through a wafer 40 having contact extensions 45 added and a polymer coating 47 completed according to an embodiment of the present invention. The wafer with all added elements has an overall thickness T and a thickness t for the silicon portion. Fig. 8b shows a grinding process in progress by which the wafer is reduced in thickness by grinding away a significant portion of the silicon portion from the backside, using a grinding wheel 49.

Fig. 8c shows the wafer after backgrinding, which now has an overall thickness T' and a thickness for the silicon portion of t' . In this example the overall thickness is reduced to less than $1/4$ of its former thickness, and the thickness of the silicon (t') is now less than the thickness of the added polymer layer. This is possible because the polymer layer is a cross-linking material when it cures, unlike the single crystal silicon, and the polymer layer is quite a lot stronger in every direction than the silicon.

A practical result of such backgrinding according to the present invention is that overall weight is reduced, thermal mass is reduced, cooling of dies in operation from the backside is now easier because the thermal thickness of the wafer is reduced, and the die or wafer is still stronger than it was before the addition of the polymer layer, and better able to endure rough handling and shock.

Final Testing of IC Die in Wafer Form

Final testing of finished IC dies is a process very well-known in the art. As is known in the art, there are a number of ways dies are finished; that is, provided with means to be operated by interconnection with external circuitry. As one example, dies are separated from the wafer upon which they are created, and then bonded to lead frames. Fine wires are bonded to the interface pads on the die and also to extensions of the lead frame. Each die is then encapsulated in a polymer material and each encapsulated assembly is trimmed from the lead frame. A portion of the lead frames

provide strong conductors extending outside the encapsulation material for use in soldering the assembly to such as a printed circuit board.

In another example solder balls are bonded to contact pads of each die, and these solder balls are then the contact interface to other circuitry. This practice is
5 described in some detail in this disclosure, and is well-known in the art as Ball Grid Array (BGA) technology.

In any case, final testing, which must always be done before ICs are delivered to customers, is done after the die are separated from the wafer. Although some very limited circuit testing is done in wafer form by what is known as Probe Testing, the
10 complicated final testing cannot be done at this point, because the contacts pads on the die on the wafer cannot support the mechanical consequences of probe testing. Further, the final testing that is done conventionally requires complicated robotic equipment for handling the individual finished die packages and making the necessary contacts for the testing to occur.

15 In an embodiment of the present invention final testing of die functions is performed on die before die separation from the wafer and final packaging. The added strength and integrity provided by the unique protective polymer layer makes this possible and practical.

Fig. 9 is a simplified diagram of a wafer 40 upon which a plurality of dies
20 (ICs) have been formed, as is known in the art. As the die are not at this point separated from the wafer, two die are indicated by element numbers 69 and 71, each having two contacts points, 73 and 75 for die 69, and 77 and 79 for die 71. There are, of course, many more contacts than those shown, and the elements are not shown in scale in Fig. 9.

25 In Fig. 9 contact regions 73, 75, 77, and 79 are the exposed regions of contact extensions added to wafer 40 and exposed in the planarizing process performed on polymer layer 47. Also as previously described, the polymer material is by nature much stronger than the silicon material, and provides lateral support for the interfaces between the contact extensions added and the original contacts to IC devices on the
30 wafer.

In Fig. 9 a probe device 81 is indicated as having probes 83 and 85 in contact with contact regions 77 and 79, and having a connection to testing apparatus. The drawing is representative only, and it will be apparent to the skilled artisan that the probe apparatus may in fact have many more probe extensions, and there are many ways,
5 known in the art, that probe apparatus may be implemented.

The issue in the present embodiment is that polymer layer 47 stiffens and strengthens the wafer assembly, and provides contact pads supported by the added polymer layer such that the action of the probe does not damage the surface of the wafer or any of the structures of die on the wafer, and now final testing of the die may
10 be done before separation of the die from the wafer.

In another embodiment the probe apparatus is not limited to a single die as indicated in Fig. 9, but may have probe extensions for testing multiple dies at the same time. Further, the wafer may be translated in any direction to reposition die for testing, or the probe apparatus may be moved laterally in any direction between tests
15 to reposition for testing as yet untested die on the wafer.

Testing by probe for final testing of all functions of die while the die are still a part of the wafer eliminated many steps that are otherwise necessary, such as handling finished and packaged ICs in a testing process after the die are separated from the wafer, and eliminates a need for ever performing the packaging and finishing tests for
20 those die that do not pass the final testing in the wafer form.

It will be apparent to one with skill in the art that the method and apparatus of the present invention may be provided for a wide variety of shapes and sizes of BGA assemblies and other assemblies without departing from the spirit and scope of the present invention. Similarly, the method and apparatus of the present invention may
25 be applied to BGA assemblies of varying materials. The method and apparatus of the present invention provides an automated and efficient way to apply an additional protective coating to BGA assemblies. Further, in some aspects the thickness and bulk may be significantly reduced, and the way that material is removed may vary widely. In still other aspects final testing may be done in a wide variety of ways.
30 Hence the method and apparatus of the present invention should be afforded the

broadest scope possible under examination. The spirit and scope of the present invention should be limited only by the claims that follow.

What is claimed is:

1. A method for decreasing the mass and increasing the strength of an IC wafer
5 assembly, comprising the steps of
 - (a) adding a polymer coating to the frontside of the wafer assembly to protect and strengthen; and
 - (b) removing silicon material from the backside of the wafer assembly,
10 reducing the overall thickness of the assembly.
2. The method of claim 1 wherein, in step (b), the silicon material is removed by grinding.
3. The method of claim 1 wherein, in step (a), the polymer layer is applied by one of
15 screening, spraying, dispense and spinning, or injection into a mold.
4. The method of claim 1 further comprising steps for adding contact extensions to contact regions before adding the polymer coating, and planarizing the polymer coating after addition to expose the contact extensions.
- 20 5. The method of claim 4 further comprising a step for adding second contact extensions from the exposed contact extensions after planarizing.
6. An IC die, comprising:
 - 25 contact extensions added to contact regions on a front surface at contact interfaces;
 - a polymer layer on the front surface supporting, protecting and strengthening the extensions and contact interfaces; and
 - a silicon portion having a thickness significantly less than conventional
30 silicon-based dies.

7. The IC die of claim 6 wherein the thickness of the silicon portion is less than the thickness of the polymer layer.

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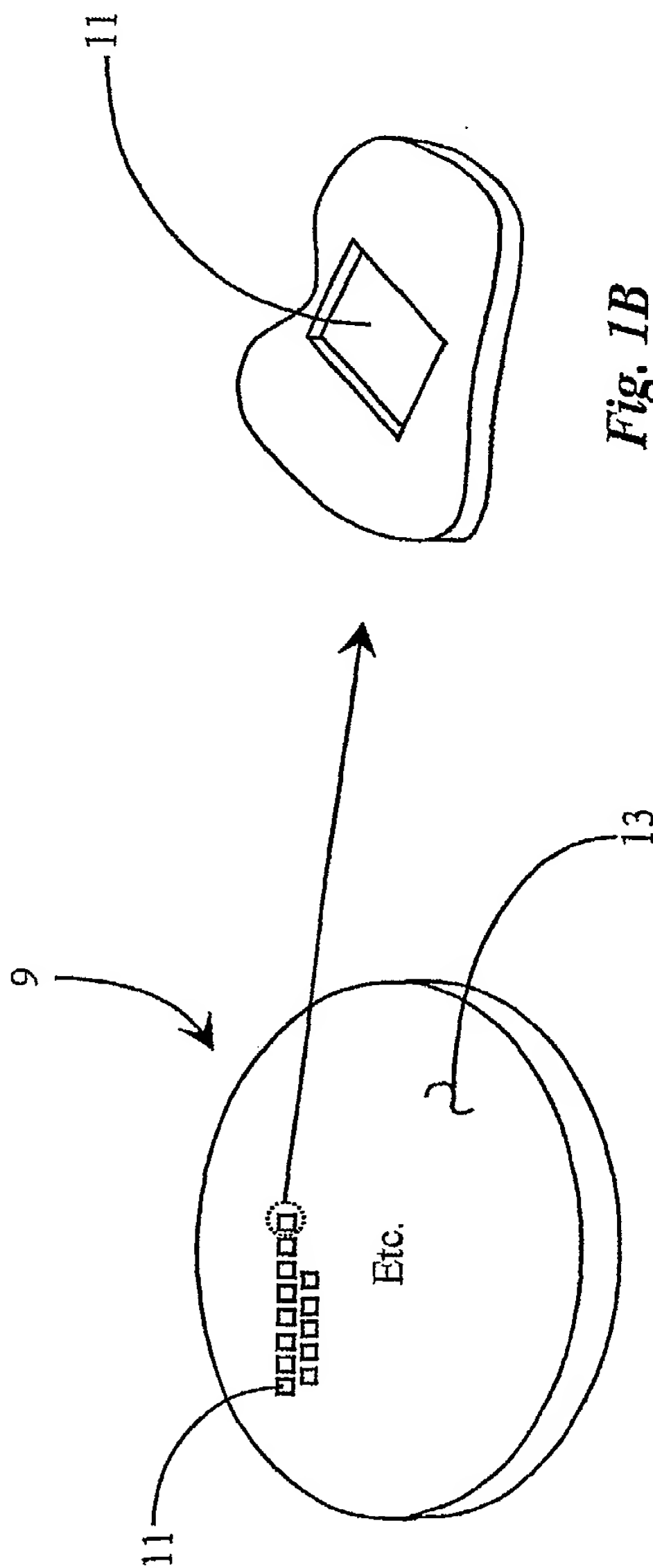


Fig. 1B
Prior Art

Fig. 1A
Prior Art

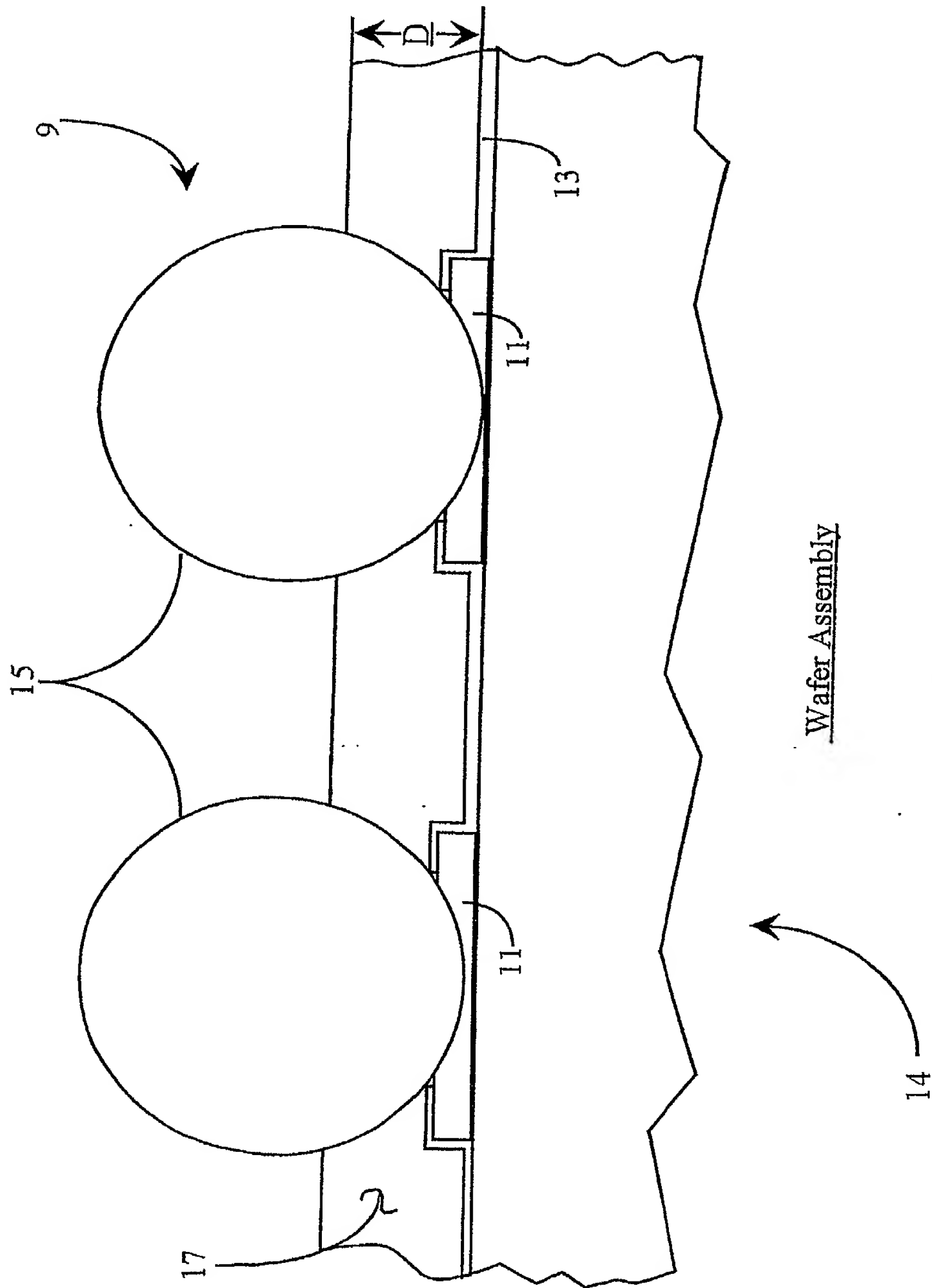


Fig. 2

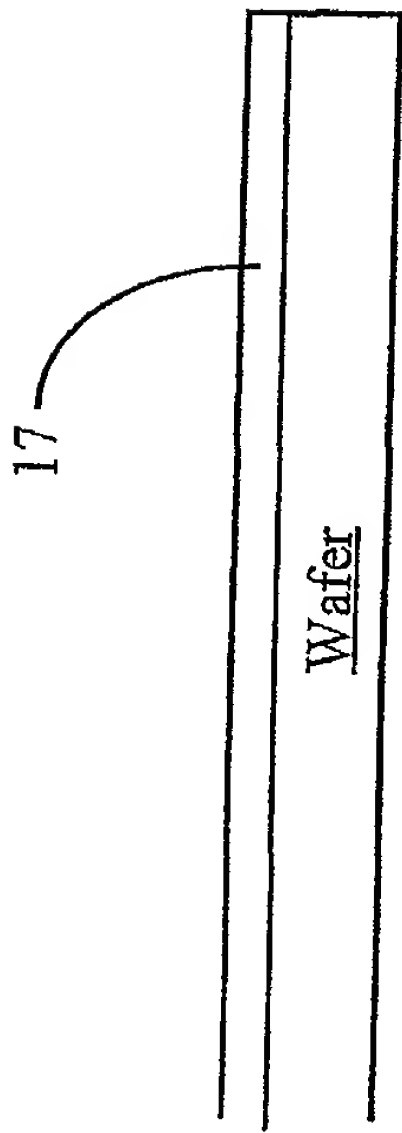


Fig. 3A

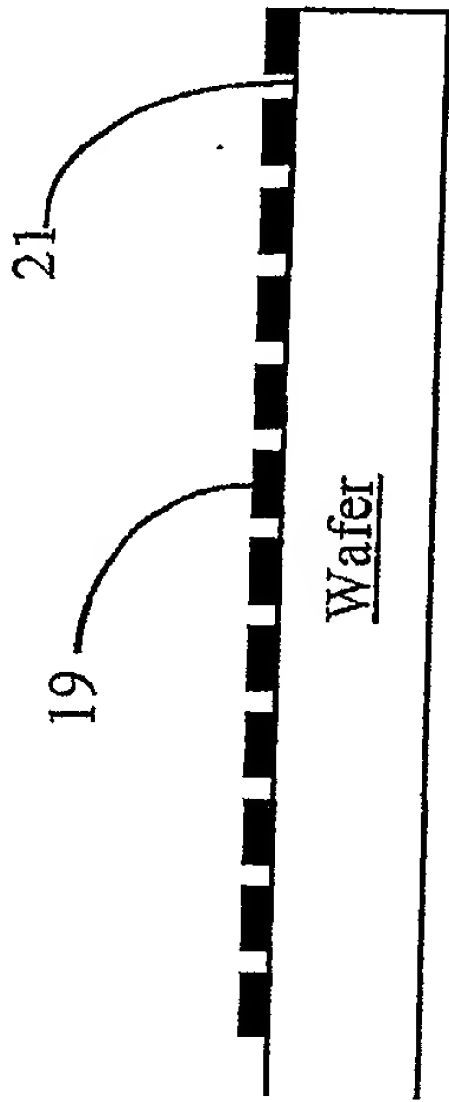


Fig. 3B

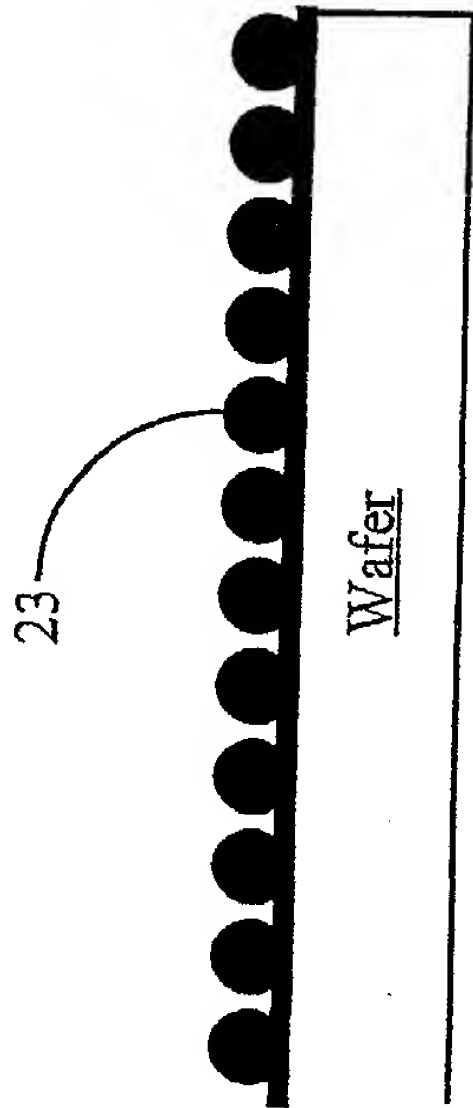


Fig. 3C

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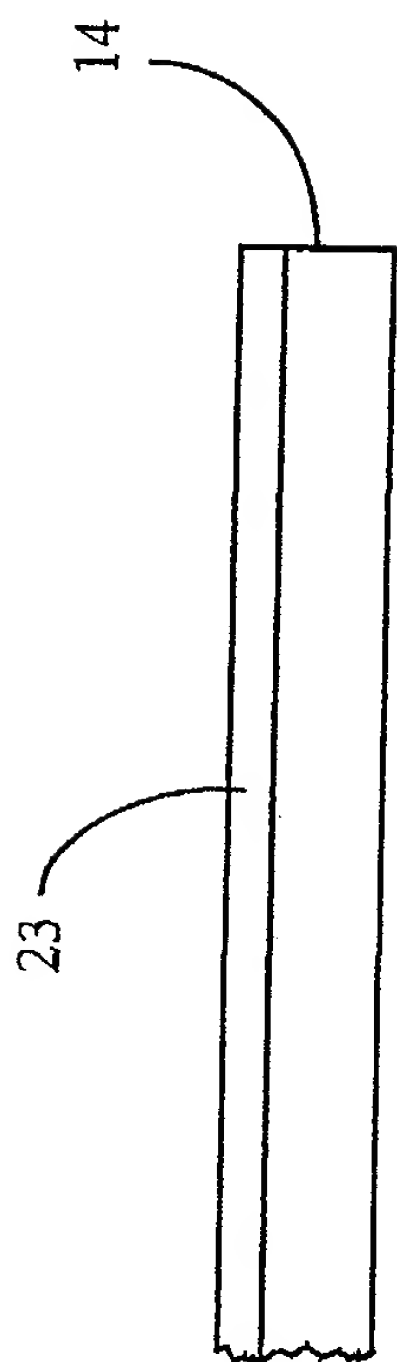


Fig. 4a

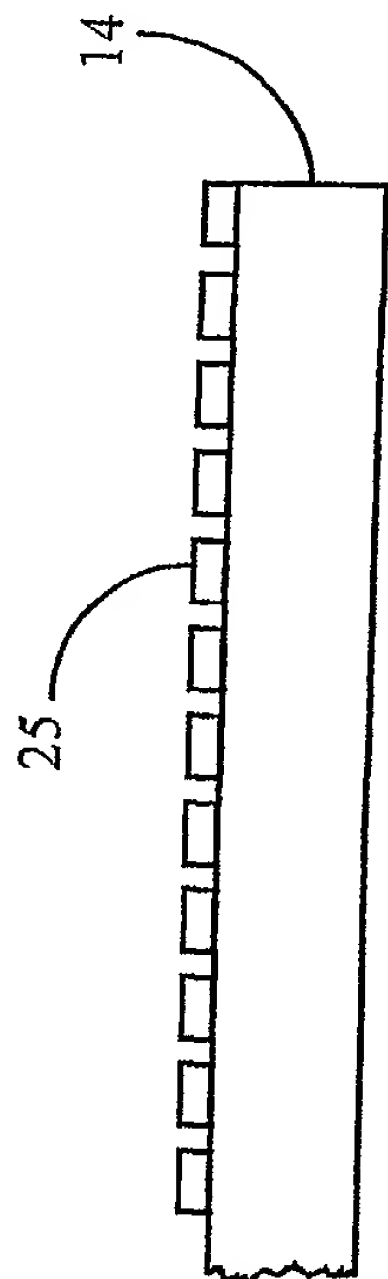


Fig. 4b

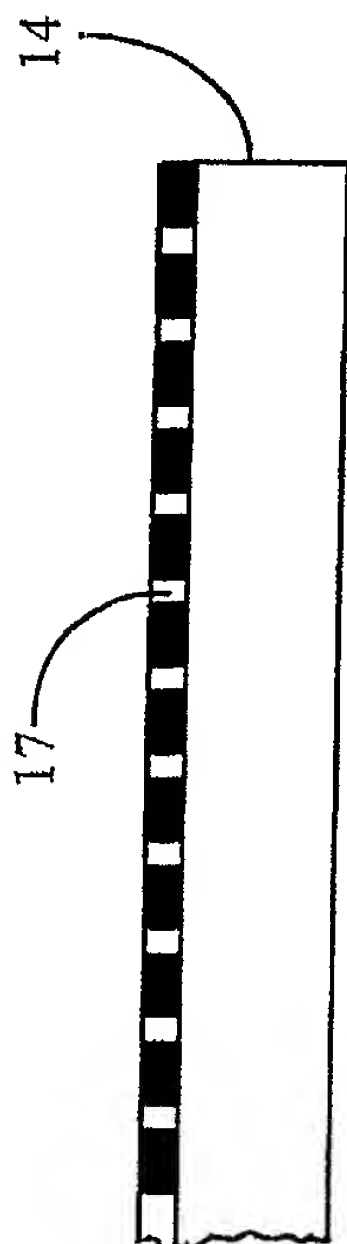


Fig. 4c

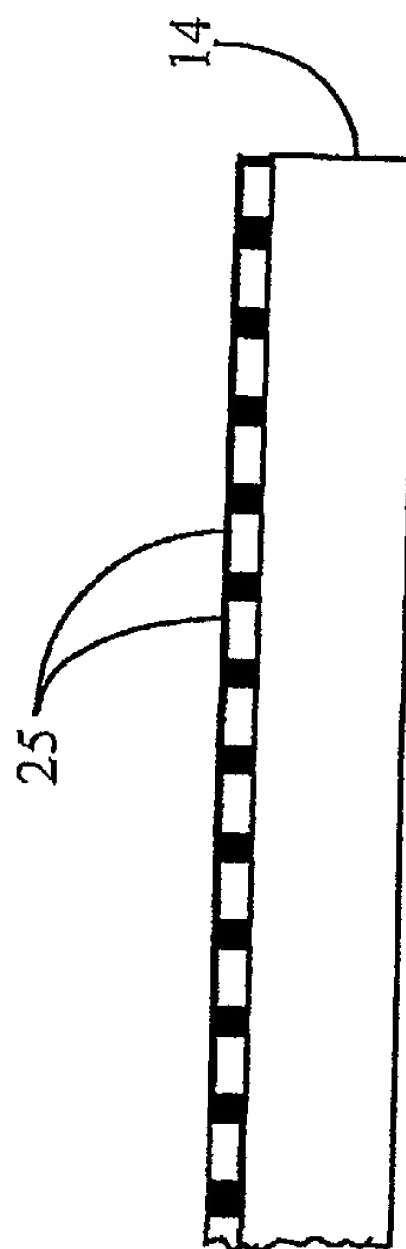


Fig. 4d

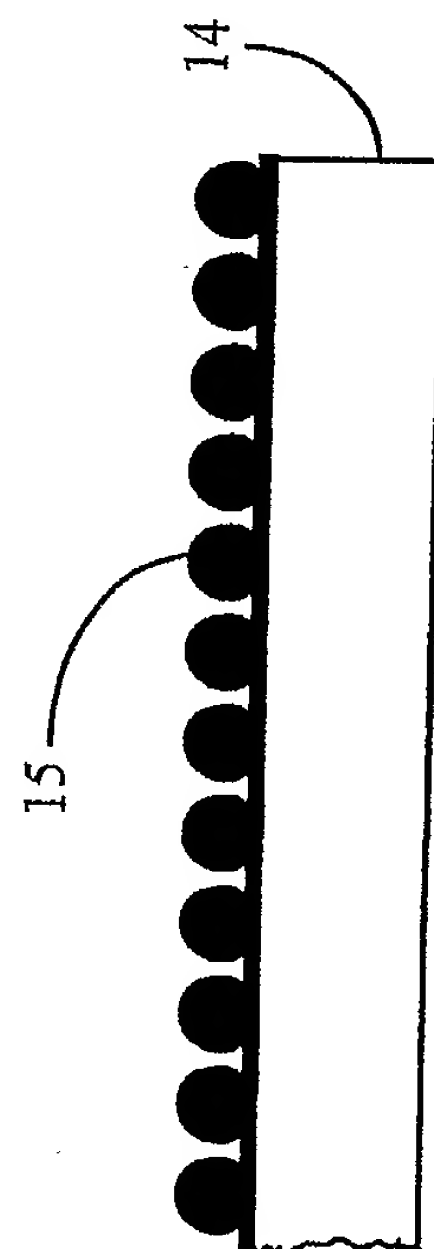


Fig. 4e

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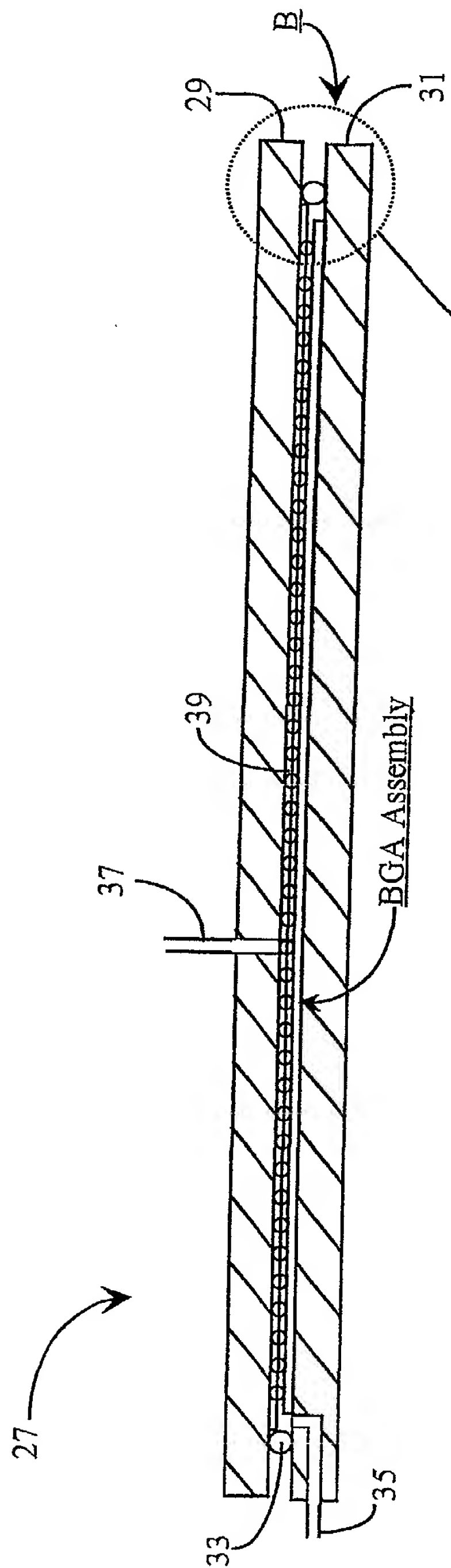


Fig. 5A

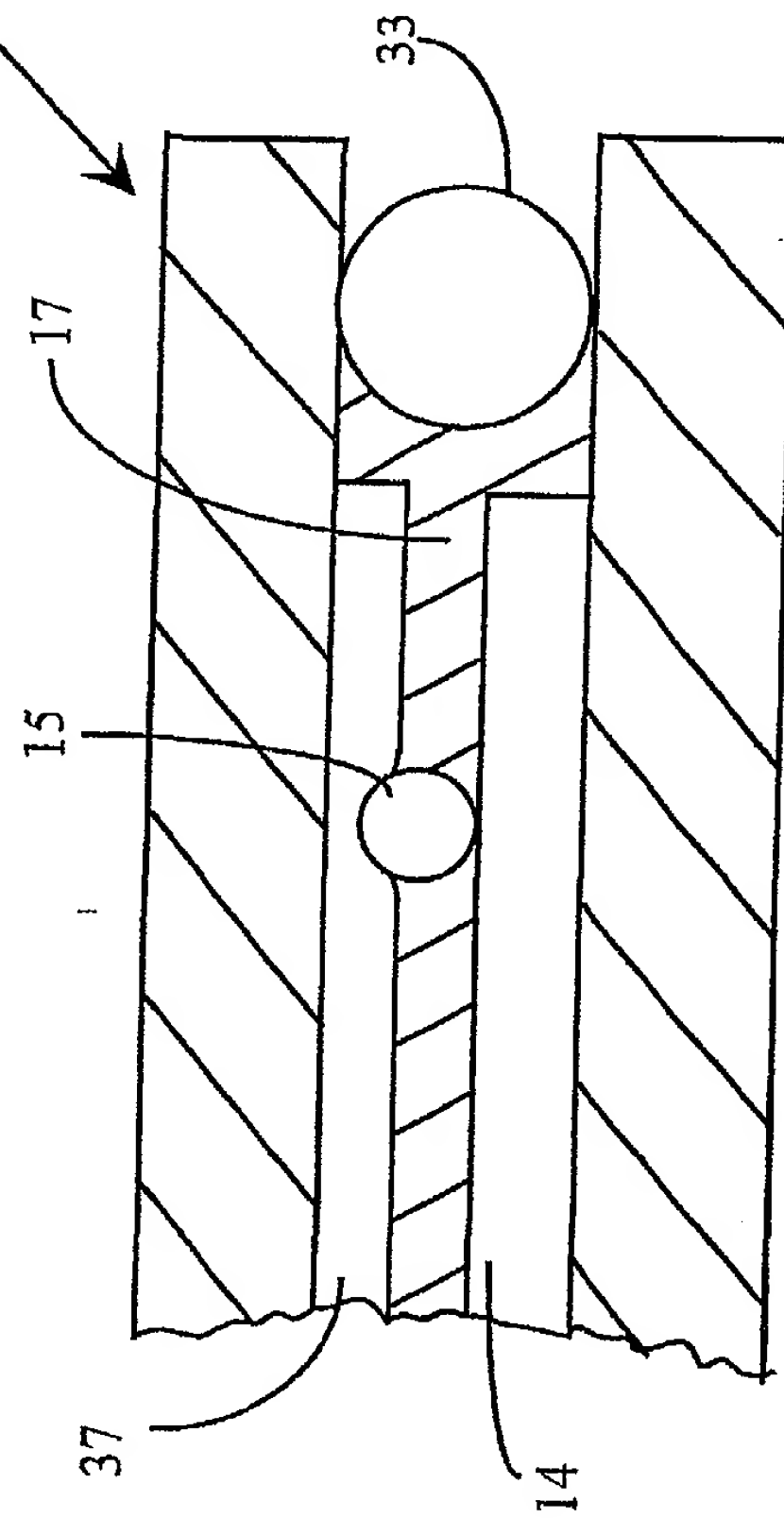


Fig. 5B

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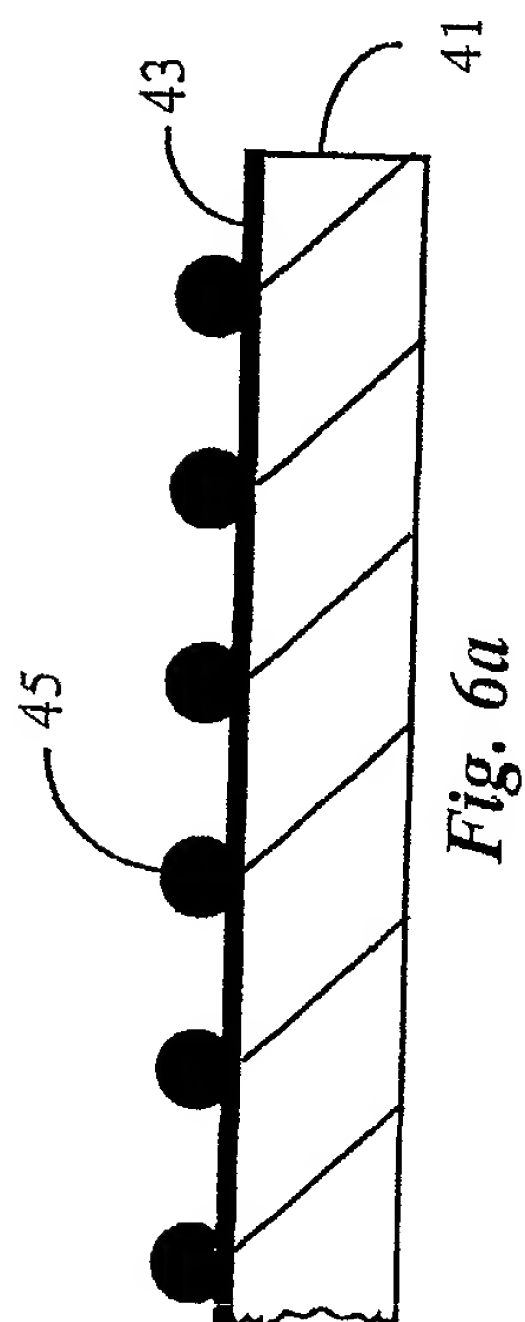


Fig. 6a

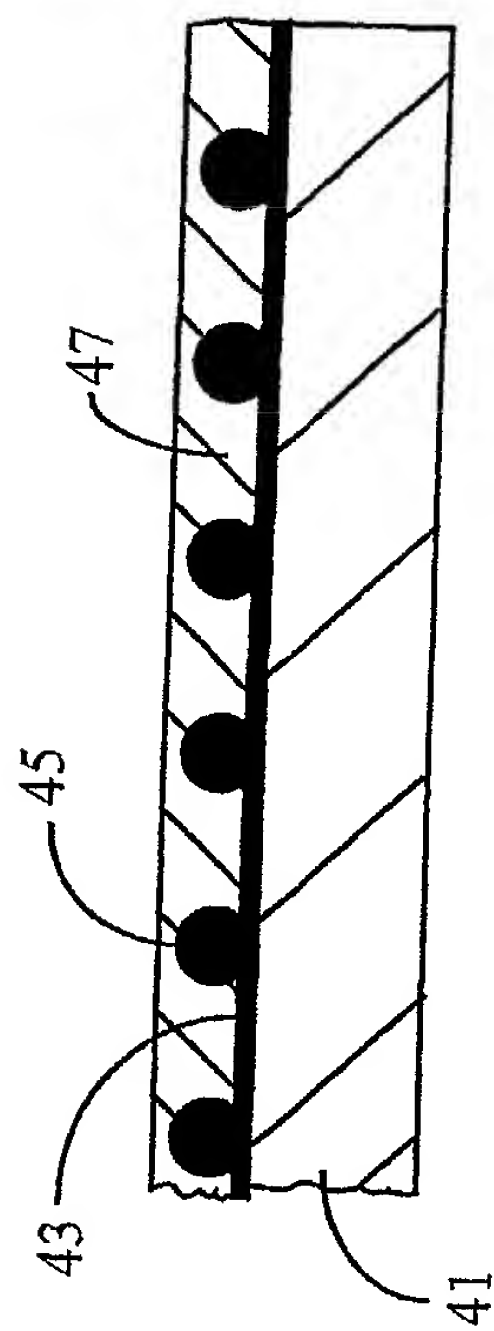


Fig. 6b

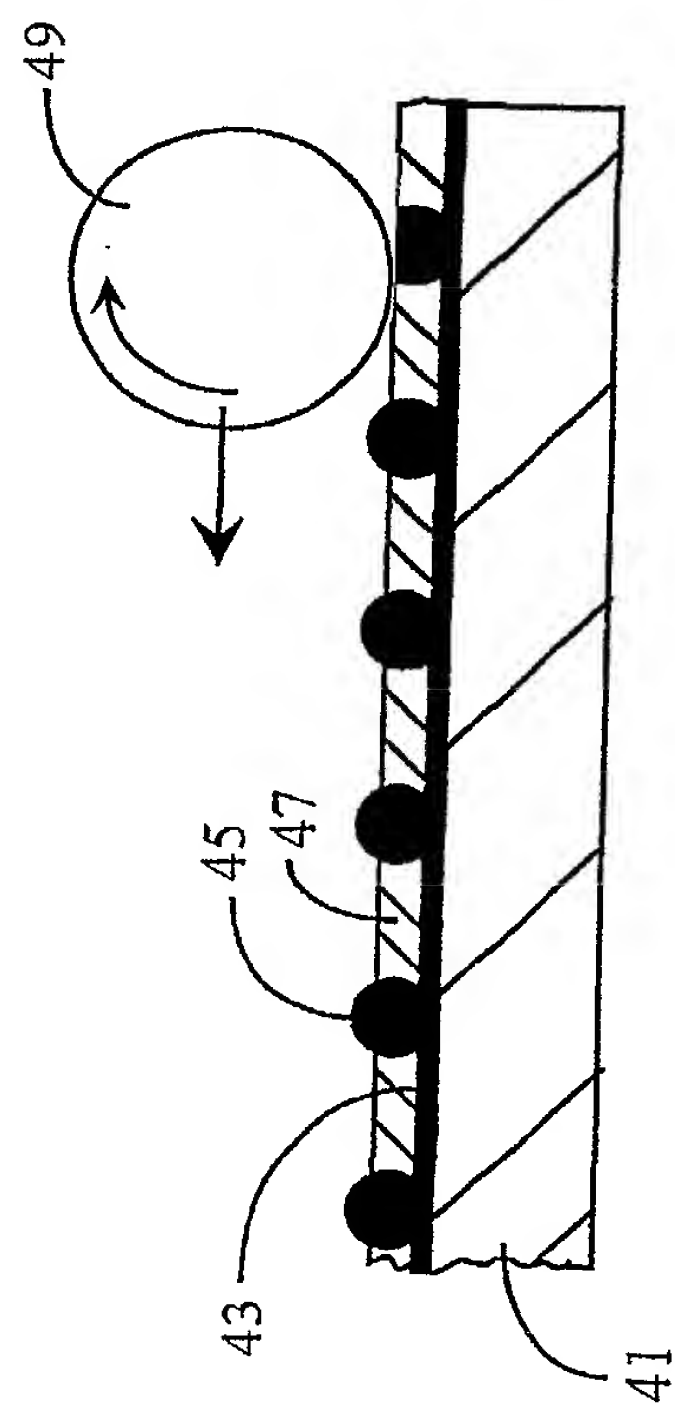


Fig. 6c

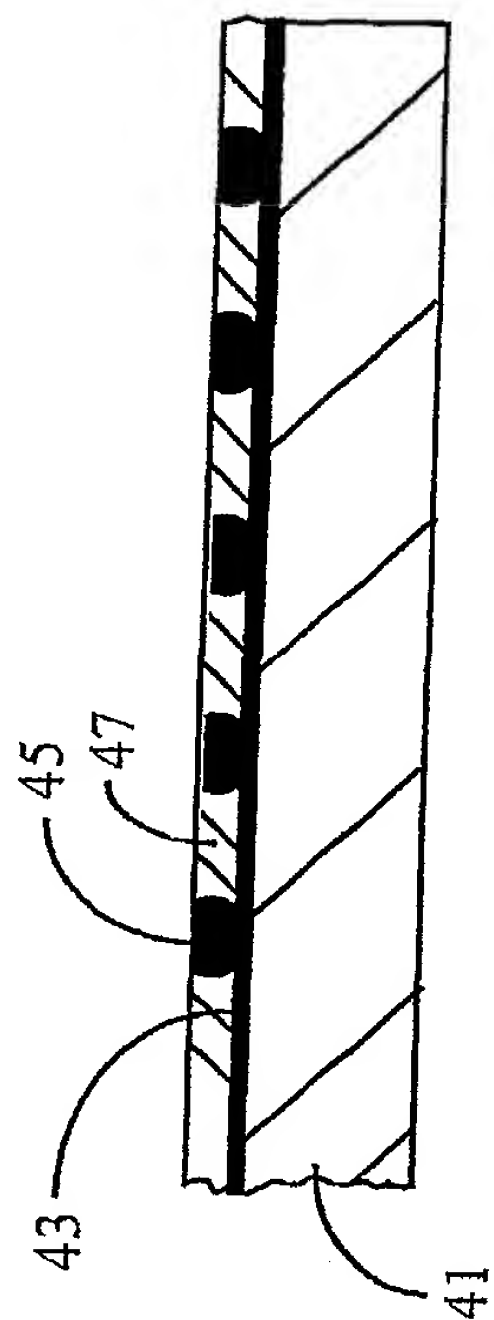


Fig. 6d

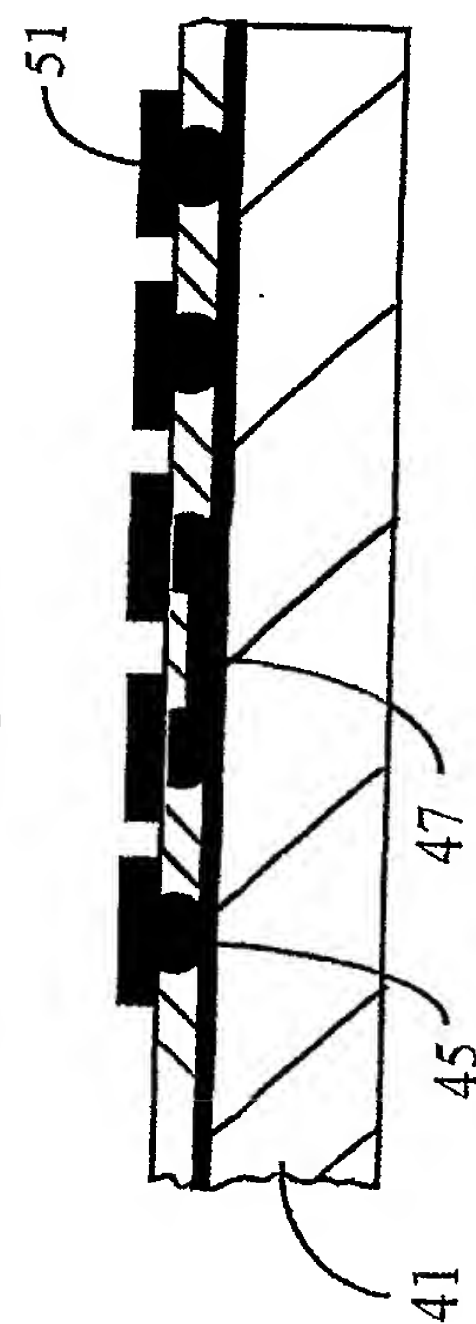


Fig. 6e

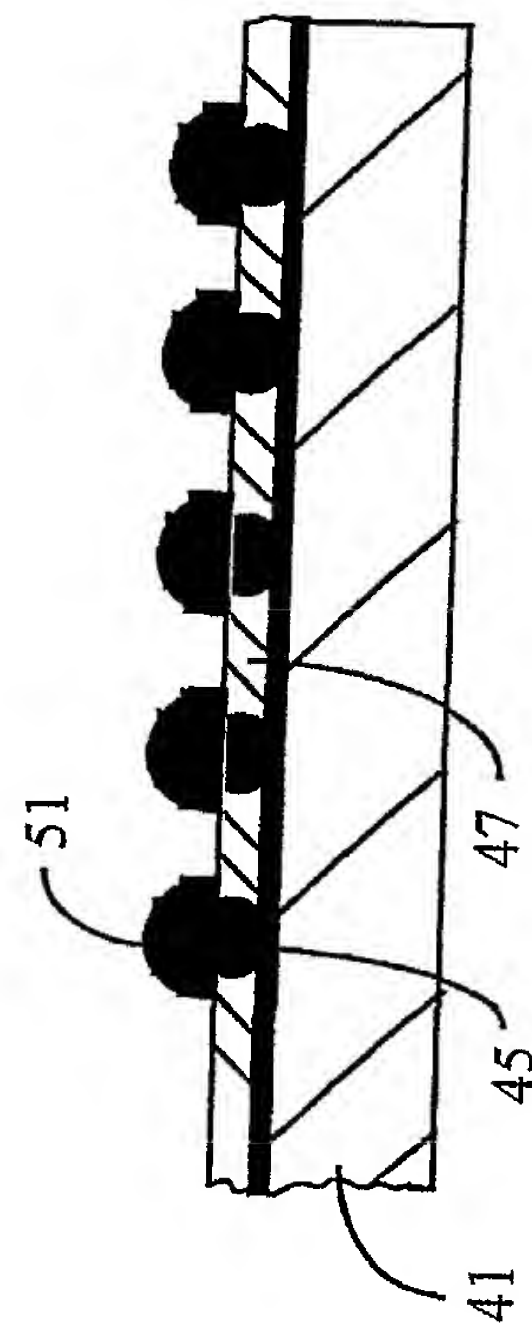


Fig. 6f

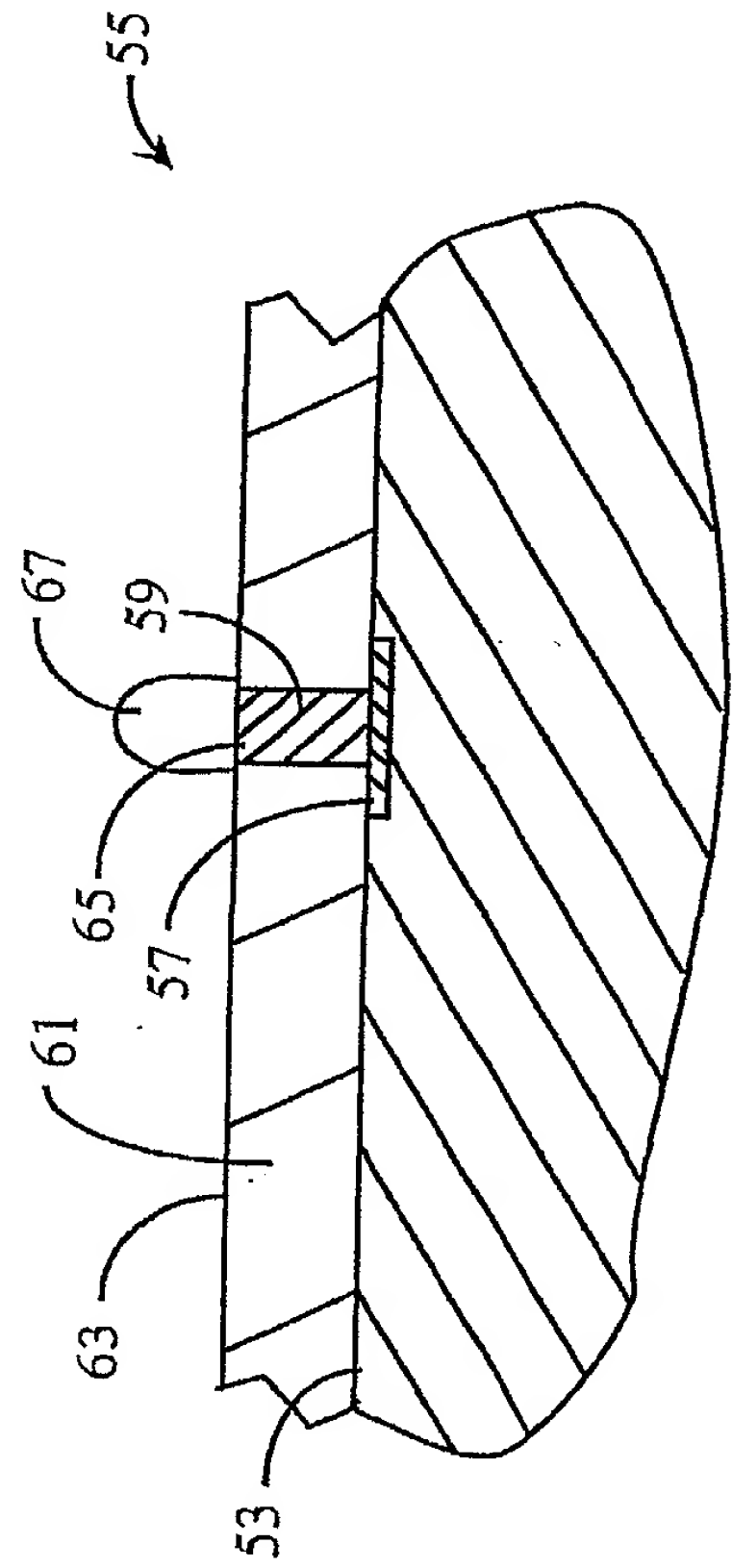


Fig. 7

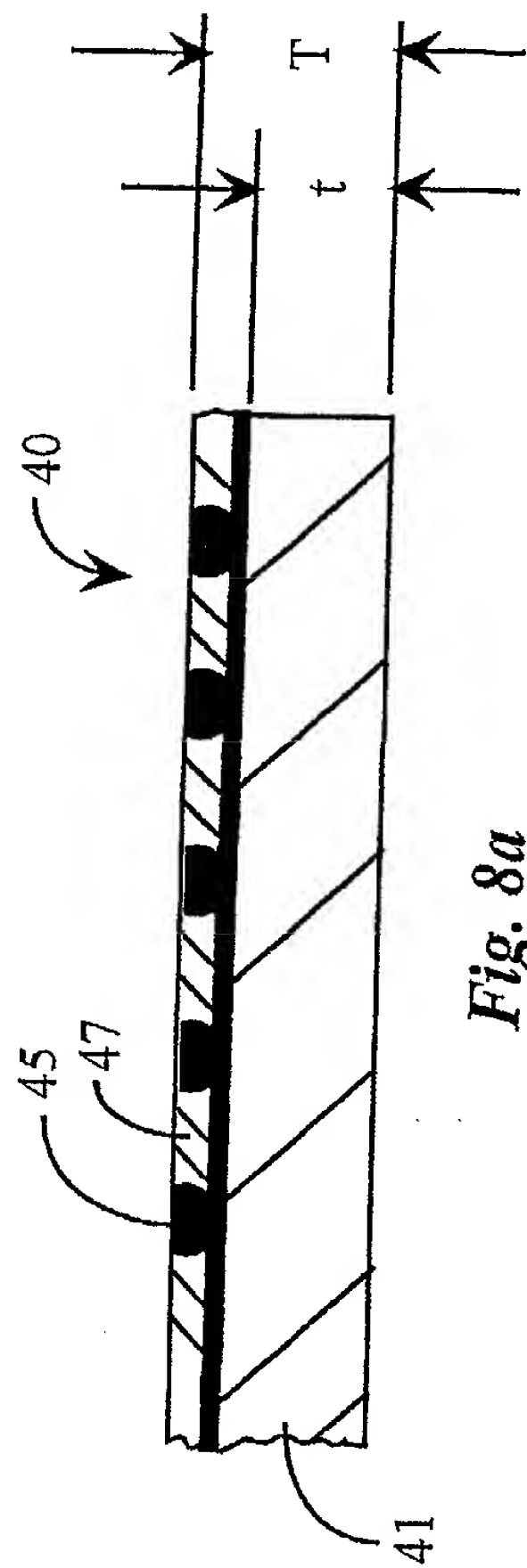


Fig. 8a

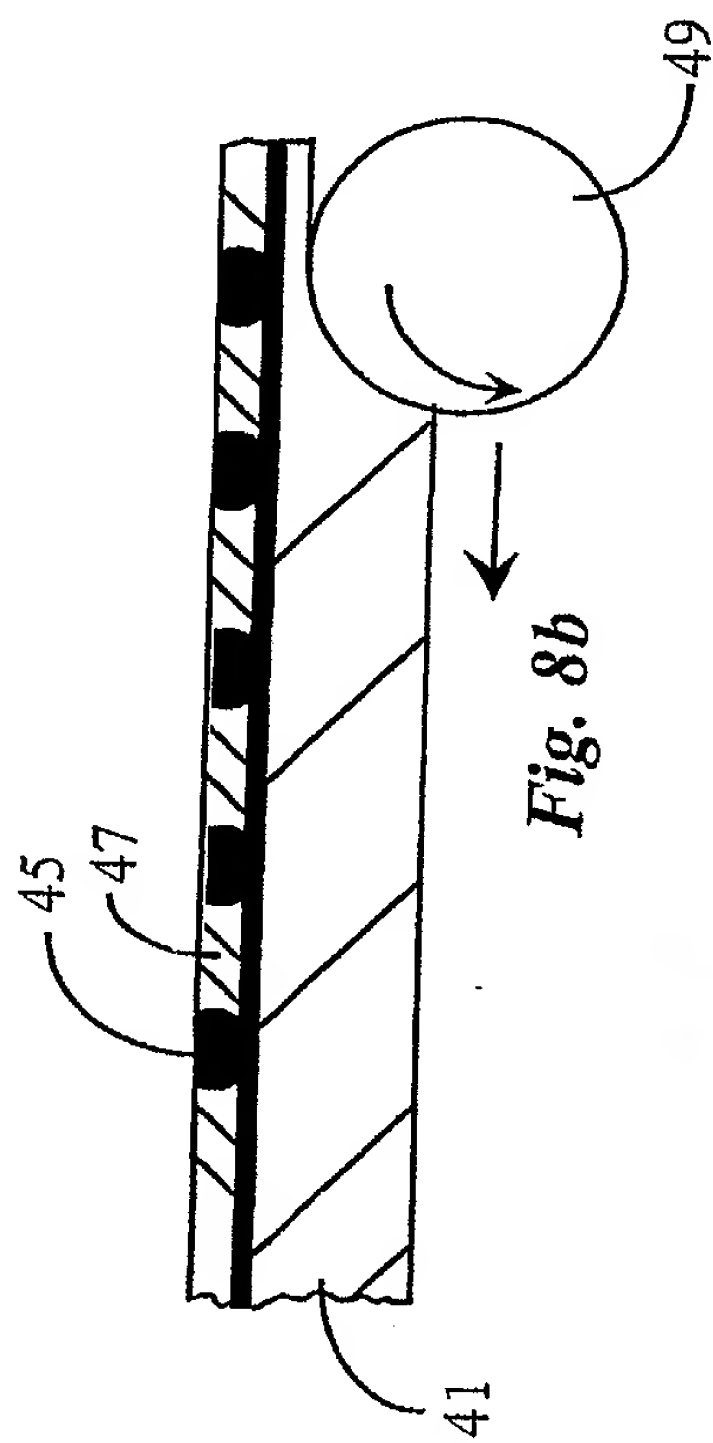


Fig. 8b

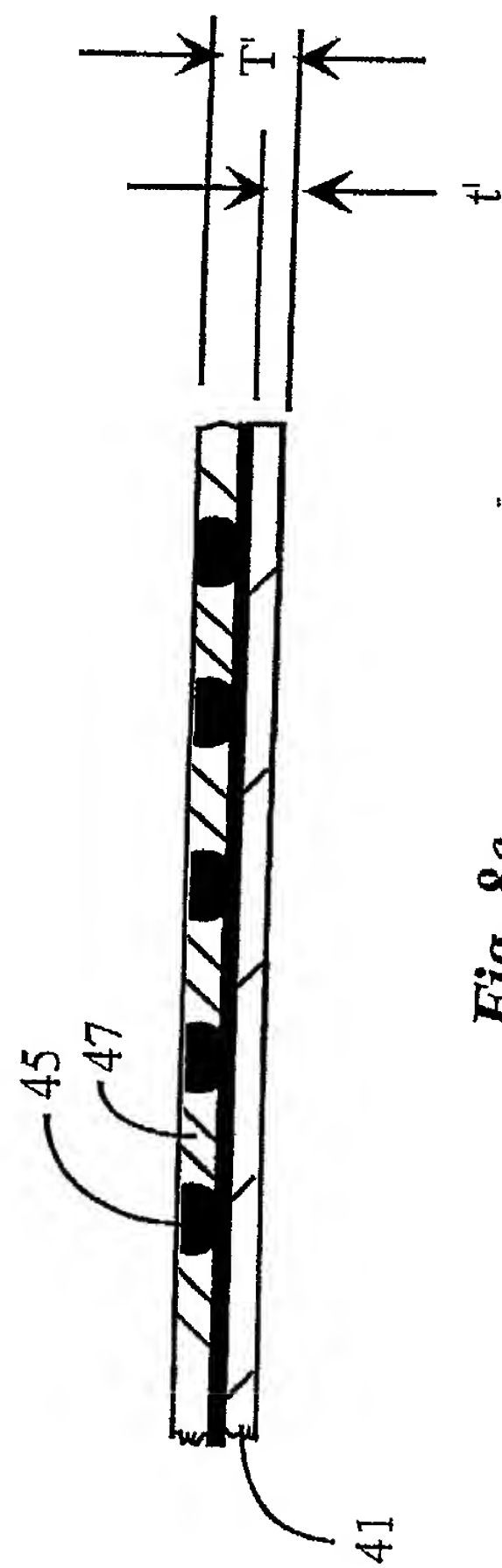


Fig. 8c

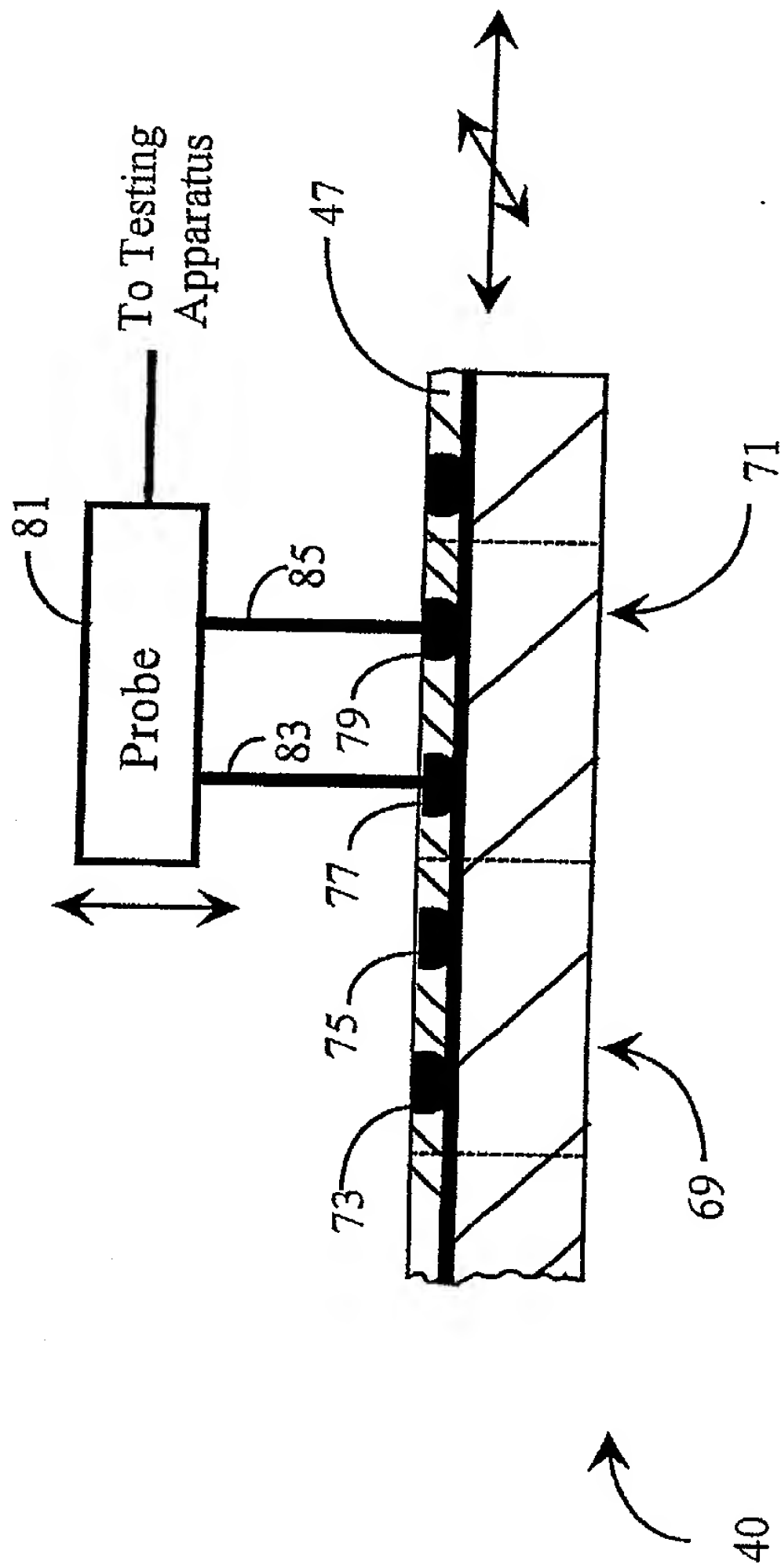


Fig. 9